

Description

The ZXMP6A13FTA uses advanced trench technology and design to provide excellent $R_{\rm DS(ON)}$ with low gate charge. This device is well suited for use as a load switch or in PWM applications.

D S S

General Features

 V_{DS} =-60V,I $_{D}$ =-2A

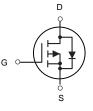
 $R_{DS(ON)}$ <160m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <200m Ω @ V_{GS} =-4.5V

Application

Load switch

PWM application



P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
ZXMP6A13FTA	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-60	V
V _G s	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	-2	А
Ідм	Drain Current-Pulsed (Note 1)	-8	А
P _D	Maximum Power Dissipation	1.5	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	83.3	°C/W



Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA -60 -		-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-60V,V _{GS} =0V -		-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	Characteristics (Note 3)					
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-1.4	-2.0	-2.6	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =-10V, I_{D} =-1.5A	-	140	160	mΩ
Diam-Source On-State Resistance		V _{GS} =-4.5V, I _D =-1.5A	-	160	200	mΩ
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-1.5A	-	3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	\/ - 20\/\/ -0\/	-	444.2	-	PF
Output Capacitance	Coss	V_{DS} =-30V, V_{GS} =0V, F=1.0MHz	-	19.6	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.UIVIDZ	-	17.9	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	40	-	nS
Turn-on Rise Time	t _r	V_{DD} =-30V, I_{D} =-1.5A,	-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$	V_{GS} =-10 V , R_{G} =3 Ω	-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q_g	V - 20 I - 4 FA	-	11.3	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-30,I _D =-1.5A, V _{GS} =-10V	-	2.7	-	nC
Gate-Drain Charge	Q_{gd}	VGS10V	-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.5A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-1.6	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F =- 1.5A	-	25		nS
Reverse Recovery Charge	Qrr	$di/dt = -100A/\mu s^{(Note3)}$	-	31		nC

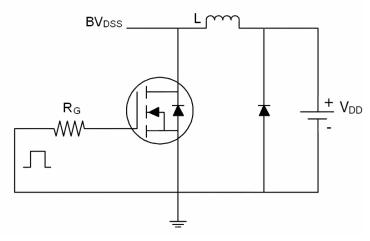
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

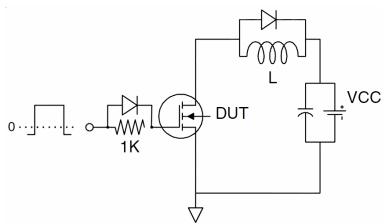


Test Circuit

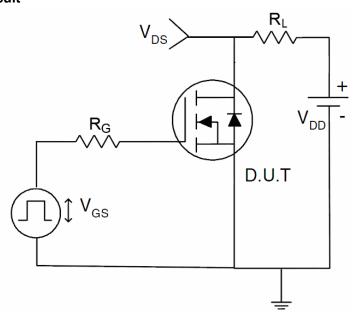
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

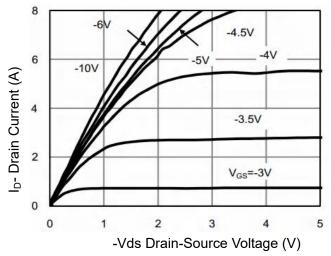


Figure 1 Output Characteristics

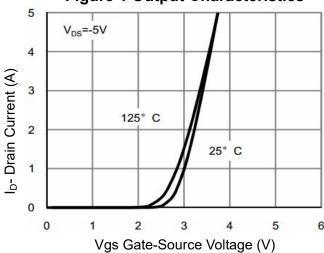
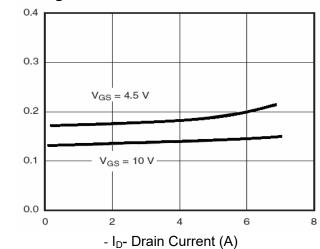


Figure 2 Transfer Characteristics



Rdson On-Resistance(()

Figure 3 Rdson- Drain Current

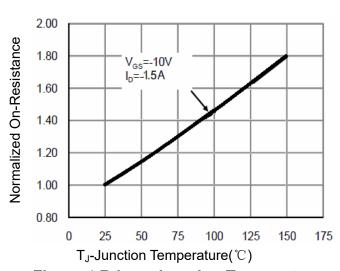
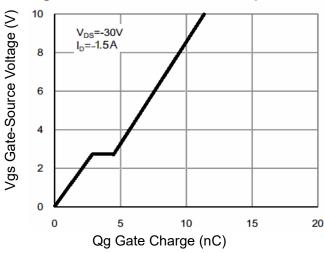


Figure 4 Rdson-Junction Temperature



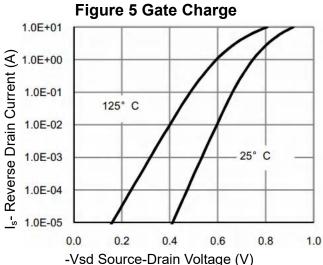


Figure 6 Source- Drain Diode Forward



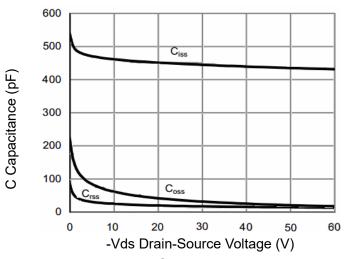


Figure 7 Capacitance vs Vds

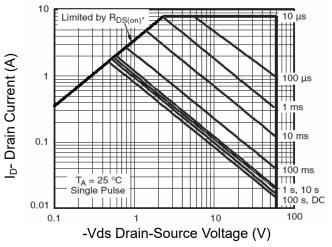


Figure 8 Safe Operation Area

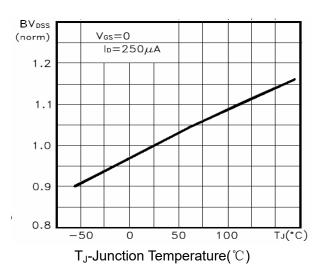


Figure 9 BV_{DSS} vs Junction Temperature

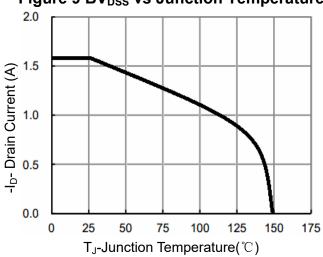
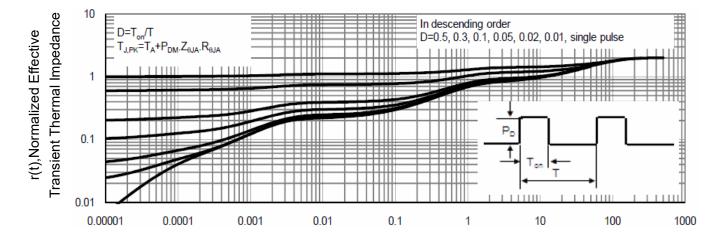


Figure 10 ID Current De-rating

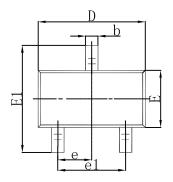


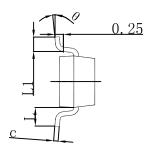
Square Wave Pluse Duration(sec)

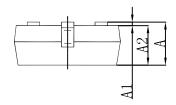
Figure 11 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

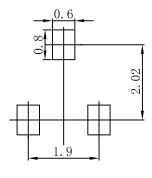






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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